

Title (en)

INJECTOR OF SILICON FOR THE SEMICONDUCTOR INDUSTRY

Title (de)

INJEKTOR AUS SILIZIUM FÜR DIE HALBLEITERINDUSTRIE

Title (fr)

INJECTEUR EN SILICIUM POUR L'INDUSTRIE DES SEMI-CONDUCTEURS

Publication

EP 3394317 A1 20181031 (DE)

Application

EP 16816680 A 20161219

Priority

- AT 8152015 A 20151222
- EP 2016081788 W 20161219

Abstract (en)

[origin: WO2017108714A1] An injector (1), which is produced from silicon and allows gas to be introduced into process chambers in processes, in particular processes in semiconductor technology, is proposed. The injector (1) is formed as a tube (2), which if appropriate consists of at least two pieces of tube (10) and in which outlet openings for the gas to be introduced into the process chamber are provided. At least one channel (4) is provided in the tube (2) that serves as an injector (1). The profile of the tube (2) serving as the injector (1) is unround, and therefore deviates from a circular profile, with elongated, triangular or star-shaped forms being possible options.

IPC 8 full level

C23C 16/455 (2006.01)

CPC (source: AT EP KR US)

C23C 16/00 (2013.01 - AT); **C23C 16/4485** (2013.01 - US); **C23C 16/45578** (2013.01 - EP KR US); **C23C 16/4583** (2013.01 - US); **H01L 21/67017** (2013.01 - US)

Citation (search report)

See references of WO 2017108714A1

Designated contracting state (EPC)

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Designated extension state (EPC)

BA ME

DOCDB simple family (publication)

WO 2017108714 A1 20170629; AT 518081 A4 20170715; AT 518081 B1 20170715; DE 212016000248 U1 20180731; EP 3394317 A1 20181031; JP 2019503086 A 20190131; KR 20180095073 A 20180824; US 2019055652 A1 20190221

DOCDB simple family (application)

EP 2016081788 W 20161219; AT 8152015 A 20151222; DE 212016000248 U 20161219; EP 16816680 A 20161219; JP 2018552122 A 20161219; KR 20187020897 A 20161219; US 201616065227 A 20161219